

Form PTO-1449
(Rev. 8-83)U.S. Department of Commerce
Patent and Trademark OfficeAttorney Docket No.
740756-2419Serial No. Not Yet
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INFORMATION DISCLOSURE STATEMENT

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10/035441
01/04/02

Applicant: Naoaki YAMAGUCHI et al.

Filing Date: January 4, 2002 Group: 1746

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
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✓	4,469,551	09/04/1984	Laude			

Examiner *Anita Laude*Date Considered *2/10/03*

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FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	<u>Translation</u> <u>Yes</u> <u>No</u>	
✓	05-243576	09/21/1993	Japan	—	—	Abstract	
✓	08-051078	02/20/1996	Japan	—	—	Abstract	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
✓	F. Ueno, "Observation of fast microscopic phase change phenomena of chalcogenide thin films", Japanese Journal of Applied Physics, Supplement, Vol. 26, Supplement 26-4, pp. 55-60, 1987.						
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Examiner	Initials <u>Unita Stevens</u>			Date Considered <u>2/10/03</u>			
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				Application Number	10/035,441
				Filing Date	January 4, 2002
				First Named Inventor	Naoaki YAMAGUCHI et al.
				Group Art Unit	1746
				Examiner Name	Unassigned
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